

<b>Notice of References Cited</b>			Application No. <b>09/285,773</b>	Applicant(s) <b>Mercaldi et al.</b>		
			Examiner <b>Lynette T. Umez-Eronini</b>	Group Art Unit <b>1765</b>	Page 1 of 1	
<b>U.S. PATENT DOCUMENTS</b>						
	DOCUMENT NO.	DATE	NAME		CLASS	SUBCLASS
A						
B						
C						
D						
E						
F						
G						
H						
I						
J						
K						
L						
M						
<b>FOREIGN PATENT DOCUMENTS</b>						
	DOCUMENT NO.	DATE	COUNTRY	NAME	CLASS	SUBCLASS
N	51123739A	10/1976	Japan	Mitsubishi Electronic Corp.	CO9K	13/08
O						
P						
Q						
R						
S						
T						
<b>NON-PATENT DOCUMENTS</b>						
	DOCUMENT (Including Author, Title, Source, and Pertinent Pages)					DATE
U	Mitsubiah Electric Corp., Etchant for silicon with minimal undercutting - of aq. hydrogen fluoride and nitric acid, with acid or organic cpd. of viscosity greater than water, English translation of JP 51123739 A					10/1976
V						
W						
X						